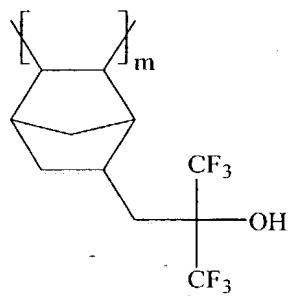


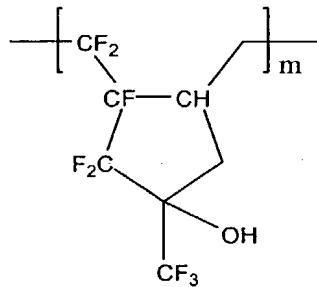
What is Claimed is:

1. A light absorption depressant comprising:  
5 a TIMD (tetraisopropyl methylene diphosphonate) which depresses light absorption at a wavelength of less than 200nm.
2. The light absorption depressant according to claim 1, wherein the wavelength is 157 nm or 193 nm.  
10
3. A photoresist composition comprising a TIMD (tetraisopropyl methylene diphosphonate).
4. The photoresist composition according to claim 3 further comprising  
15 a base resin and wherein the TIMD is present in an amount ranging from 0.01 to 25 wt% based on the base resin.
5. The photoresist composition according to claim 4, wherein the TIMD is present in an amount ranging from 0.01 to 20 wt% based on the base resin.  
20
6. The photoresist composition according to claim 3, wherein the TIMD is added in the photoresist composition for a 157 nm light source or for a 193 nm light source.
7. The photoresist composition according to claim 3, which comprises  
25 (1) a poly(norbornenehexafluoroalcohol) represented by Formula 2 or (2) a blend polymer of polymers represented by Formula 3a and Formula 3b as a base resin.

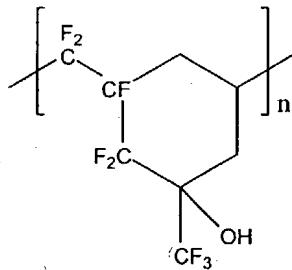
Formula 2



Formula 3a



5 Formula 3b



8. The photoresist composition according to claim 7, wherein the composition is a chemically amplified photoresist composition comprising a photoacid 10 generator.

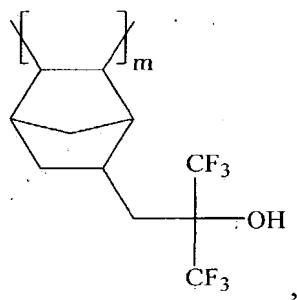
9. A process for forming a photoresist pattern, comprising:  
(a) coating the photoresist composition of claim 3 on an underlying layer to form a photoresist film;  
15 (b) baking the photoresist film, and then exposing the baked photoresist film to light;  
(c) baking the exposed photoresist film; and  
(d) developing the baked photoresist film to obtain a photoresist pattern.

10. A semiconductor device manufactured according to the process of  
claim 9.

11. A photoresist composition comprising a hydrocarbon compound  
5 including P=O groups.

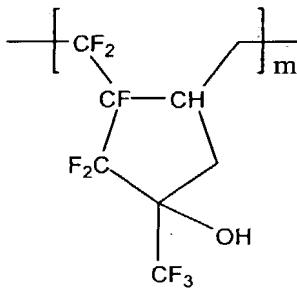
12. A photoresist composition comprising a TIMD (tetraisopropyl  
methylene diphosphonate) and a base resin selected from the group consisting of

Formula 2

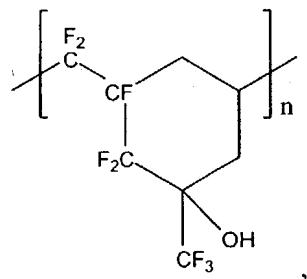


10

Formula 3a



Formula 3b



and mixtures thereof.

5

13. The photoresist composition according to claim 12, wherein the TIMD is present in an amount ranging from 0.01 to 25 wt% based on the base resin.

10 14. The photoresist composition according to claim 13, wherein the TIMD is present in an amount ranging from 0.01 to 20 wt% based on the base resin.

15 15. The photoresist composition according to claim 12, wherein the TIMD is added in the photoresist composition for a 157 nm light source or for a 193 nm light source.

16

16. The photoresist composition according to claim 15, wherein the composition is a chemically amplified photoresist composition comprising a photoacid generator.

20

17. A process for forming a photoresist pattern, comprising:

(a) coating the photoresist composition of claim 12 on an underlying layer to form a photoresist film;

(b) baking the photoresist film, and then exposing the baked photoresist film to light;

25

(c) baking the exposed photoresist film; and

(d) developing the baked photoresist film to obtain a photoresist pattern.

18. The photoresist composition according to claim 12 further comprising a hydrocarbon compound including P=O groups.

19. A semiconductor device manufactured according to the process of  
claim 17.